# Octal 3-State Non-Inverting Buffer/Line Driver/ Line Receiver With LSTTL-Compatible Inputs

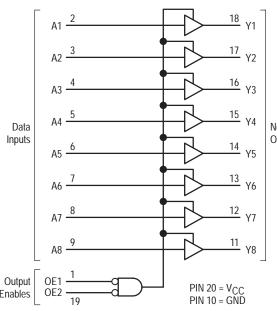
**High-Performance Silicon-Gate CMOS** 

The MC74HCT541A is identical in pinout to the LS541. This device may be used as a level converter for interfacing TTL or NMOS outputs to high speed CMOS inputs.

The HCT541A is an octal non-inverting buffer/line driver/line receiver designed to be used with 3-state memory address drivers, clock drivers, and other bus-oriented systems. This device features inputs and outputs on opposite sides of the package and two ANDed active-low output enables.

- Output Drive Capability: 15 LSTTL Loads
- TTL/NMOS-Compatible Input Levels
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 4.5 to 5.5V
- Low Input Current: 1µA
- In Compliance With the JEDEC Standard No. 7A Requirements
- Chip Complexity: 134 FETs or 33.5 Equivalent Gates

### **LOGIC DIAGRAM**



Non-Inverting Outputs



http://onsemi.com





PDIP-20 P SUFFIX CASE 738





SOIC WIDE-20 DW SUFFIX CASE 751D



= Assembly Location

WL = Wafer Lot

YY = Year

WW = Work Week

### ORDERING INFORMATION

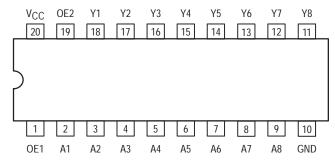
Device	Package	Shipping
MC74HCT541AN	PDIP-20	1440 / Box
MC74HCT541ADW	SOIC-WIDE	38 / Rail
MC74HCT541ADWR2	SOIC-WIDE	1000 / Reel

### **FUNCTION TABLE**

	Inputs	Output V	
OE1	OE2	Α	Output Y
L	L	L	L
L	L	Н	Н
Н	Х	Х	Z
Х	Н	Х	Z

Z = High Impedance X = Don't Care

### Pinout: 20-Lead Packages (Top View)



### **MAXIMUM RATINGS\***

Symbol	Parameter	Value	Unit
VCC	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V <sub>in</sub>	DC Input Voltage (Referenced to GND)	- 0.5 to V <sub>CC</sub> + 0.5	V
V <sub>out</sub>	DC Output Voltage (Referenced to GND)	- 0.5 to V <sub>CC</sub> + 0.5	V
l <sub>in</sub>	DC Input Current, per Pin	± 20	mA
l <sub>out</sub>	DC Output Current, per Pin	± 35	mA
ICC	DC Supply Current, V <sub>CC</sub> and GND Pins	± 75	mA
PD	Power Dissipation in Still Air Plastic DIP† SOIC Package†	750 500	mW
T <sub>stg</sub>	Storage Temperature Range	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds Plastic DIP or SOIC Package	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V<sub>CC</sub>). Unused outputs must be left open.

SOIC Package:  $-~7~mW/^{\circ}C$  from  $65^{\circ}$  to  $125^{\circ}C$ 

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

### RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
Vcc	DC Supply Voltage (Referenced to GND)		5.5	V
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Referenced to GND)	0	VCC	V
T <sub>A</sub>	Operating Temperature Range, All Package Types	- 55	+ 125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise/Fall Time (Figure 1)	0	500	ns

## DC CHARACTERISTICS (Voltages Referenced to GND)

			VCC	Guara	nteed Lin	nit	
Symbol	Parameter	Condition	V	−55 to 25°C	≤85°C	≤125°C	Unit
VIH	Minimum High–Level Input Voltage	$V_{\text{out}} = 0.1 \text{V or V}_{\text{CC}} - 0.1 \text{V}$ $ I_{\text{out}}  \le 20 \mu \text{A}$	4.5 5.5	2.0 2.0	2.0 2.0	2.0 2.0	V
VIL	Maximum Low–Level Input Voltage	$V_{Out} = 0.1V \text{ or } V_{CC} - 0.1V$ $ I_{Out}  \le 20 \mu A$	4.5 5.5	0.8 0.8	0.8 0.8	0.8 0.8	V
VOH	Minimum High–Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \le 20 \mu A$	4.5 5.5	4.4 5.4	4.4 5.4	4.4 5.4	V
		$V_{in} = V_{IH} \text{ or } V_{IL} \qquad  I_{out}  \le 6.0 \text{mA}$	4.5	3.98	3.84	3.70	
V <sub>OL</sub>	Maximum Low–Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \le 20 \mu A$	4.5 5.5	0.1 0.1	0.1 0.1	0.1 0.1	V
		$V_{in} = V_{IH} \text{ or } V_{IL} \qquad  I_{out}  \le 6.0 \text{mA}$	4.5	0.26	0.33	0.40	
l <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = V <sub>CC</sub> or GND	5.5	±0.1	±1.0	±1.0	μΑ
l <sub>OZ</sub>	Maximum Three–State Leakage Current	Output in High Impedance State Vin = VIL or VIH Vout = VCC or GND	5.5	±0.5	±5.0	±10.0	μΑ
lcc	Maximum Quiescent Supply Current (per Package)	V <sub>in</sub> = V <sub>CC</sub> or GND I <sub>out</sub> = 0μA	5.5	4	40	160	μΑ
ΔlCC	Additional Quiescent Supply Current	V <sub>in</sub> = 2.4V, Any One Input		≥ <b>–55</b> °C	25 to 1	125°C	
	Current	$V_{in} = V_{CC}$ or GND, Other Inputs $I_{out} = 0\mu A$	5.5	2.9	2.	4	mA

<sup>1.</sup> Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

<sup>\*</sup>Maximum Ratings are those values beyond which damage to the device may occur.

Functional operation should be restricted to the Recommended Operating Conditions.

<sup>†</sup>Derating — Plastic DIP: - 10 mW/°C from 65° to 125°C

<sup>2.</sup> Total Supply Current =  $I_{CC} + \Sigma \Delta I_{CC}$ .

**AC CHARACTERISTICS** ( $V_{CC} = 5.0V$ ,  $C_L = 50$  pF, Input  $t_f = t_f = 6$  ns)

		Gu	aranteed Lim	nit	
Symbol	Parameter	–55 to 25°C	≤85°C	≤125°C	Unit
tPLH, tPHL	Maximum Propagation Delay, Input A to Output Y (Figures 1 and 3)	23	28	32	ns
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Maximum Propagation Delay, Output Enable to Output Y (Figures 2 and 4)	30	34	38	ns
t <sub>PZL</sub> , t <sub>PZH</sub>	Maximum Propagation Delay, Output Enable to Output Y (Figures 2 and 4)	30	34	38	ns
tTLH, tTHL	Maximum Output Transition Time, Any Output (Figures 1 and 3)	12	15	18	ns
C <sub>in</sub>	Maximum Input Capacitance	10	10	10	pF
C <sub>out</sub>	Maximum Three–State Output Capacitance (Output in High Impedance State)	15	15	15	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V <sub>CC</sub> = 5.0 V		
$C_{PD}$	Power Dissipation Capacitance (Per Buffer)*	55	pF	

<sup>\*</sup> Used to determine the no–load dynamic power consumption:  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ . For load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

### **SWITCHING WAVEFORMS**

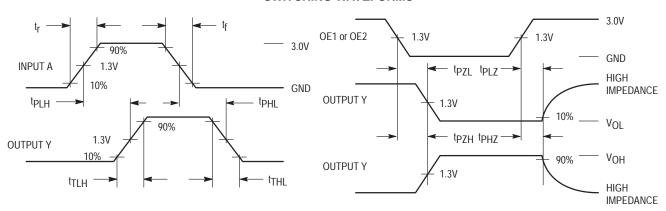
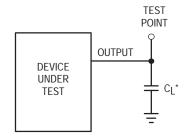


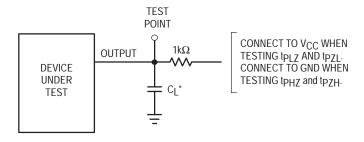
Figure 1. Figure 2.

### **TEST CIRCUITS**



\*Includes all probe and jig capacitance

Figure 3.



\*Includes all probe and jig capacitance

Figure 4.

### **PIN DESCRIPTIONS**

### **INPUTS**

A1, A2, A3, A4, A5, A6, A7, A8 (PINS 2, 3, 4, 5, 6, 7, 8, 9) — Data input pins. Data on these pins appear in non–inverted form on the corresponding Y outputs, when the outputs are enabled.

### **CONTROLS**

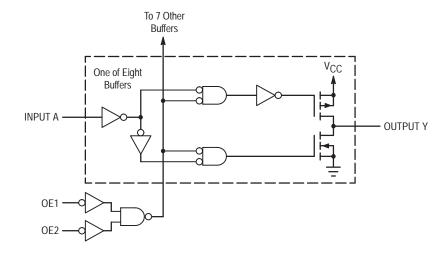
**OE1, OE2** (**PINS 1, 19**) — Output enables (active–low). When a low voltage is applied to both of these pins, the

outputs are enabled and the device functions as a non-inverting buffer. When a high voltage is applied to either input, the outputs assume the high impedance state.

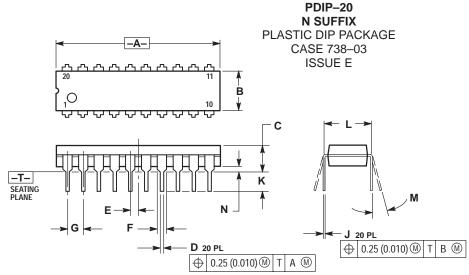
### **OUTPUTS**

Y1, Y2, Y3, Y4, Y5, Y6, Y7, Y8 (PINS 18, 17, 16, 15, 14, 13, 12, 11) — Device outputs. Depending upon the state of the output enable pins, these outputs are either non–inverting outputs or high–impedance outputs.

### **LOGIC DETAIL**



### **PACKAGE DIMENSIONS**



### NOTES:

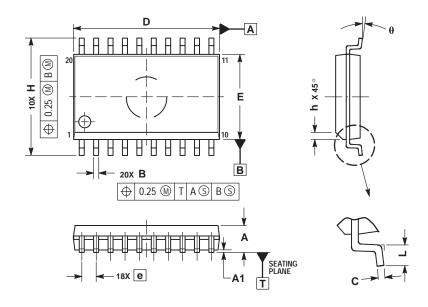
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 1 14.3W, 1702.

  CONTROLLING DIMENSION: INCH.

  DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
- 4. DIMENSION B DOES NOT INCLUDE MOLD

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	1.010	1.070	25.66	27.17
В	0.240	0.260	6.10	6.60
С	0.150	0.180	3.81	4.57
D	0.015	0.022	0.39	0.55
Ε	0.050 BSC		1.27 BSC	
F	0.050	0.070	1.27	1.77
G	0.100	BSC	2.54	BSC
J	0.008	0.015	0.21	0.38
K	0.110	0.140	2.80	3.55
L	0.300 BSC		7.62	BSC
M	0 °	15°	0°	15°
N	0.020	0.040	0.51	1.01

### SO-20 **DW SUFFIX** CASE 751D-05 ISSUE F



- NOTES:
  1. DIMENSIONS ARE IN MILLIMETERS.
  2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.

- PER ASME 174-5M, 1994.

  DIMENSIONS D AND E DO NOT INCLUDE MOLD
  PROTRUSION.

  MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
  DIMENSION B DOES NOT INCLUDE DAMBAR
  PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		
DIM	MIN	MAX	
Α	2.35	2.65	
A1	0.10	0.25	
В	0.35	0.49	
С	0.23	0.32	
D	12.65	12.95	
Е	7.40	7.60	
е	1.27	BSC	
Н	10.05	10.55	
h	0.25	0.75	
L	0.50	0.90	
Δ.	0.0	7.0	

# **Notes**

# **Notes**

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